

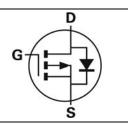
-40V P-CHANNEL Power MOSFET

V_{DSS}, -40V

 $R_{DS(ON)}$, 14 m Ω (max.) @ V_{GS}=-10V $R_{DS(ON)}$, 21 m Ω (max.) @ V_{GS}=-4.5V

 I_D , -9A





Description

The SGP4015S is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The SGP4015S meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Low On-Resistance
- Low Input Capacitance
- · Low Miller Charge
- Low Input / Output Leakage
- · Pb-free lead plating; RoHS compliant

Applications

- Motor / Body Load Control
- Automotive Systems
- Load Switch
- DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SGP4015S	Halogen-Free	SOP-8	S	Tape & Reel	3,000

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parame	Symbol	Value	Unit	
Drain-Source Voltage		V _{DS}	-40	V
Gate-Source Voltage		V _G S	±20	V
Drain Current Continuous	T _A =25°C	I-	-9	А
Drain Current-Continuous	T _A =70°C	lo l	-7.2	А
Drain Current-Pulsed Note 1		I _{DM}	-19	Α
Avalanche Current, L=0.1mH		las	-55	А
Avalanche Energy, L=0.1mH Note 3		E _{AS}	151	mJ
Maximum Dawar Dissination	T _A =25°C	P _D	1.5	W
Maximum Power Dissipation	T _A =70°C	PD P	0.9	W
Storage Temperature Range		T _{STG}	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient Note 1	Reja	Steady State	=	-	85	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	24	°C/W

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Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =-250µA	-40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-32V, V _{GS} =0V	-	-	-1	μΑ
Gate-Body Leakage	Igss	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =-250µA	-1	-	-2.5	V
Drain-Source On-State Resistance	D	V _{GS} =-10V, I _{DS} =-8A	-	12	14	mΩ
	R _{DS(ON)}	V _{GS} =-4.5V, I _{DS} =-6A	-	17	21	
Forward Transconductance Note 1	gfs	V _{DS} =-5V, I _D =-8A	-	26	-	S

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	3431	-	
Output Capacitance	Coss	V _{DS} =-20V, V _{GS} =0V, f=1MHz	-	316	-	pF
Reverse Transfer Capacitance	Crss		-	217	-	

SWITCHING CHARACTERISTICS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Turn-On Delay Time	T _{d(on)}		-	49	-		
Rise Time	t _r	V_{DD} =-20V, V_{GS} =-10V, R_{G} =3.3 Ω ,	-	34	-]	
Turn-Off Delay Time	T _{d(off)}	I _D =-8A	-	98	-	ns	
Fall Time	t _f		-	9.4	-		
Total Gate Charge at 10V	Qg	\\ - 00\\ \\ - 4.5\\	-	27	-		
Gate to Source Gate Charge	Qgs	V _{DS} =-20V, V _{GS} =-4.5V, I _D =-8A	-	7.5	-	nC	
Gate to Drain "Miller" Charge	Q_{gd}	100A	-	7.3	-		

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-8A	-	-	-1.2	V	
Body Diode Reverse Recovery Time	Is	\/-=\/-=0\/ Force Current	-	-	-9	Α	
Body Diode Reverse Recovery Charge	Ism	V _G =V _D =0V, Force Current	-	-	-20	Α	

Notes:

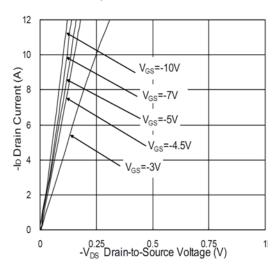
- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design. R_{BJA} shown below for single device operation on FR-4 in still air.
- 3. The EAS data shows Max. rating. The test condition is VDD=-25V, VGS=-10V, L=0.1mH, IAS=-55A



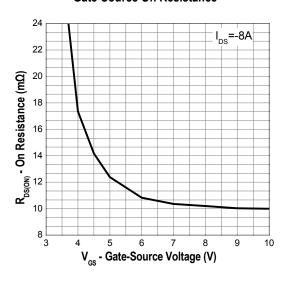
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Typical Operating Characteristics

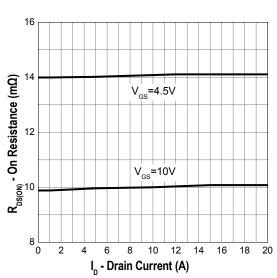
Output Characteristics



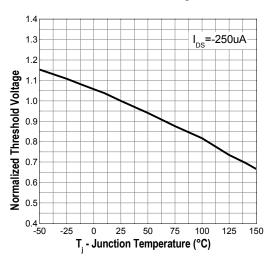
Gate-Source On Resistance



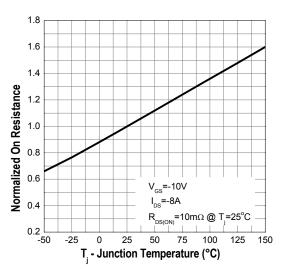
Drain-Source On Resistance



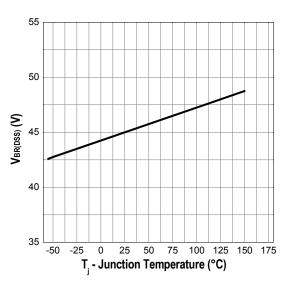
Gate Threshold Voltage



Drain-Source On Resistance



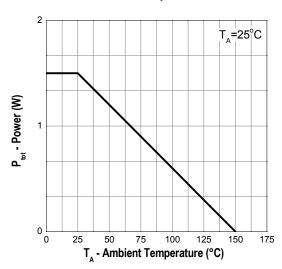
Source-Drain Diode Forward



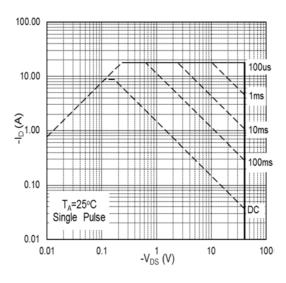


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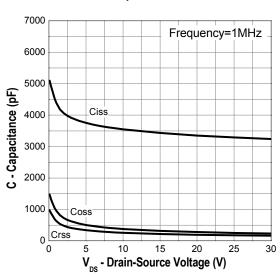
Power Dissipation



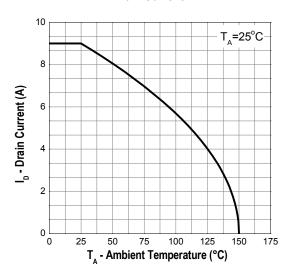
Safe Operation Area



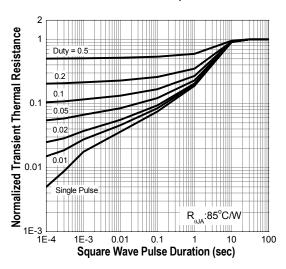
Capacitance



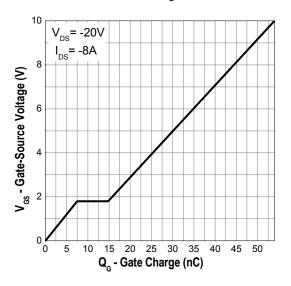
Drain Current



Transient Thermal Impedance



Gate Charge



Marking Information



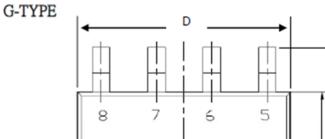
SOP-8 (S)	Marking Rule
Laser Marking SGP4015S YYMMXXX	Line 1 : Device Name SGP4015S Line 2 : Date Code YYMMXXX YY : Year Code MM : Month Code XXX : Serial Number





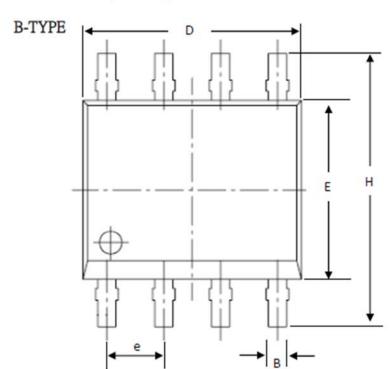


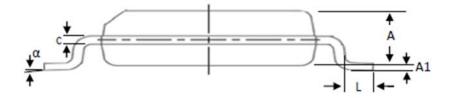
Package of Dimension



1				
- E H	5	6	7	8
	4	3	2	1
<u>'</u>				

Symbol	Min	Nor	Max
Α	1.35	1.55	1.75
A1	0.10	0.18	0.25
В	0.31	0.41	0.51
С	0.17	0.21	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
e	1.27	1.27	1.27
Н	5.80	6.00	6.20
L	0.40	0.84	1.27
α	0.00	4.00	8.00



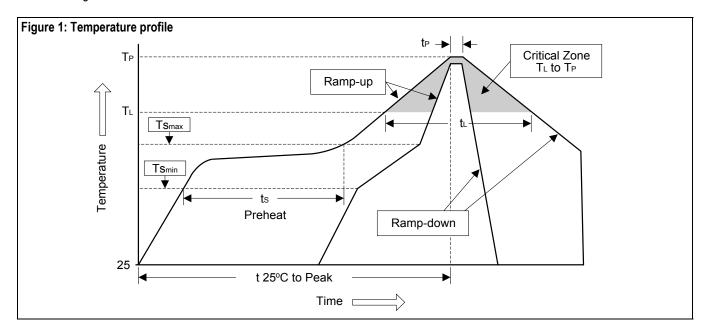




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Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t₂)	10 to 50 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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